EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	112	2002/0130311	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 10:17
S2	32	"0130311"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 10:18
S3	18	"4518456"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 10:31
S4	226	(438/707).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/17 10:47
S5	7	(light OR radiation OR signal OR optical) induced AND wet etch AND semiconductor NOT substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 11:04
S6	1084	wet etch AND semiconductor NOT substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 11:06
S7	1	self terminating AND wet etch AND semiconductor NOT substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 11:06

S8	0	light enduced etching	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 12:36
S9	9	light induced etching	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 12:36
S10	31685	quantum AND etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:10
S11	5833	quantum AND wet etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:10
S12	3814	wavelength AND quantum AND wet etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:10
S13	731	nano$5 AND wavelength AND quantum AND wet etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:11
S14	1862921	(self terminating OR self stopping OR automatic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:18

S15	454	S14 AND S11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:18
S16	413	S14 AND S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:18
S17	293	maskless AND wet etching	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:20
S18	6841	nanowire	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:21
S19	12	S17 AND S18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:21
S20	2226	quantum confinement	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:24
S21	1067	quantum confinement AND etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:24

S22	1572	quantum confinement AND wavelength	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:25
S23	762	quantum confinement AND wavelength AND etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 13:25
S24	0	("2009/0057650").URPN.	USPAT	ADJ	ON	2009/03/17 13:27
S25	0	photolithography AND wavelengths of light AND nano	USPAT	ADJ	ON	2009/03/17 13:36
S26	1838	photolithography AND nano	USPAT	ADJ	ON	2009/03/17 13:37
S27	135	photolithography AND quantum confinement	USPAT	ADJ	ON	2009/03/17 13:37
S28	260	nanowire AND control$5 WITH diameter	USPAT	ADJ	ON	2009/03/17 13:48
S29	135	nanowire AND control$5 WITH diameter AND etch	USPAT	ADJ	ON	2009/03/17 13:49
S30	0	confinement WITH nano AND radiation WITH etch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:49
S31	1965	nano$8 AND radiation WITH etch$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:49
S32	304	nano$8 AND radiation WITH etch$5 AND quantum	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:50
S33	4061	radiation WITH holes AND etch$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:53

S34	479	radiation WITH holes AND etch$5 AND nano$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:53
S35	935	radiation WITH holes AND etch$5 AND nano$8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:53
S36	206	S34 NOT mask	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:54
S37	153	S34 NOT mask NOT solar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 16:57
S38	71894	nano$8 AND etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 17:01
S39	11805	nano$8 AND etch$3 WITH (radiation OR light OR optical OR signal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 17:01
S40	226	(438/707).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/03/17 17:02

S41	12	nano$8 AND etch$3 WITH (radiation OR light OR optical OR signal) AND S40	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 17:02
S42	749	nanowire WITH diameter AND etch$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 17:07
S43	749	nanowire WITH diameter AND (etch$5 OR photolith$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/17 17:10
S44	4	((ERIK) near2 (BAKKERS)).INV.	USPAT	ADJ	ON	2009/03/17 17:25
S45	0	("7192533").URPN.	USPAT	ADJ	ON	2009/03/17 17:26
S46	5	((LOUIS) near2 (FEINER)).INV.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/03/17 17:27
S47	10	((ABRAHAM) near2 (BALKENENDE)).INV.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/03/17 17:28
S48	6	977/818	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 09:52
S49	25	977/963	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 09:58
S50	37	977/845	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 10:00

S51	48	977/887	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 10:29
S52	1419	438/99	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 10:38
S53	302	438/99 AND etch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 10:46
S54	12	photoassisted electrochemical etching	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 11:39
S55	13	photo AND etch WITH polariz$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/03/18 17:20
S56	28	size selective photoetching	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/14 09:56
S57	1939	nanowire WITH substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/01 15:07

S58	300	polar$5 AND etching AND nanowire WITH substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/01 15:09
S59	1603	etch AND nanowire	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/28 13:50
S60	0	method of AND S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/28 13:50
S61	558	etch AND nanowire AND @pd<"20060621"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/28 13:53
S62	4	electrochemical etch AND nanowire AND @pd<"20060621"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/28 13:56
S63	2	"20020130311"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/28 14:08
S64	18	"4518456"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/28 14:12

S65	1	polarize NEAR etch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/30 15:15
S66	128	polarize WITH etch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/30 15:17
S67	36	"5835221"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/30 15:53
S68	19	polarized light WITH etch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/05 14:39
S69	0	("2008/0224115").URPN.	USPAT	ADJ	ON	2009/08/05 15:47
S70	1455	etch AND substrate NEAR sample	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 14:36
S71	0	etch AND substrate NEAR electrically connected NEAR sample	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 14:37
S72	11	etch AND substrate WITH electrically connected WITH sample	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:06

S73	185	etch AND nanowires NEAR substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:12
S74	2	etch AND nanowires NEAR substrate AND etch resist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:13
S75	2	etch AND nanowire AND alkyltriethoxysiloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:15
S76	2	etch AND nanowire AND (alkyltriethoxysiloxane OR alkyltrimethoxysiloxane)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:15
S77	2	etch AND (alkyltriethoxysiloxane OR alkyltrimethoxysiloxane)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:16
S78	2	(alkyltriethoxysiloxane OR alkyltrimethoxysiloxane)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:16
S79	3466	growth AND nanowires	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:18

S80	5	"7084060"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:19
S81	2	"20020130311"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/11 15:21
S82	2	"20020130311"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/13 15:38
S83	533	nanowire NEAR substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/13 15:56
S84	80	"6359288"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/17 09:58
S85	2	alkyltriethoxysiloxane OR alkyltrimethoxysiloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/17 10:37
S86	110	"6231744"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/08/17 10:44